

WIPO IAP13  
NOV 28 2005  
PATENT & TRADEMARK OFFICE

Substitute for form 1449A/PTO				<b>Complete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (use as many sheets as necessary)				Application Number	10/777,117
				Filing Date	February 13, 2004
				First Named Inventor	Shigeharu MONOE et al.
				Art Unit	2871
				Examiner Name	Michael Manh Trinh
Sheet	1	of	1	Attorney Docket Number	740756-2714

U.S. PATENT DOCUMENTS					
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	U.S. Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code <sup>2</sup> (if known)			
MT		US-6,933,184 B2	08/23/2005	Arao et al.	
		US-6,872,604 B2	03/29/2005	Yamazaki et al.	
		US-6,706,544 B2	03/16/2004	Yamazaki et al.	
		US-6,596,571 B2	07/22/2003	Arao et al.	
		US-2004/0140472 A1	07/22/2004	Fujimoto et al.	
		US-2003/0100151 A1	05/29/2003	Okamoto	
		US-2003/0062524 A1	04/03/2003	Kimura	
		US-2003/0020118 A1	01/30/2003	Kajiwarra et al.	
		US-2002/0163049 A1	11/07/2002	Yamazaki et al.	
		US-2001/0048408 A1	12/06/2001	Koyama et al.	
		US-2005/0181610 A1	08/18/2005	Sasagawa et al.	
		US-2004/0209409 A1	10/21/2004	Monoe et al.	

FOREIGN PATENT DOCUMENTS						
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>4</sup>
		Country Code <sup>3</sup> Number <sup>3</sup> Kind Code <sup>3</sup> (if known)				

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
MT		OHGATA, K. et al., "A New Dopant Activation Technique for Poly-Si TFTs with a Self-Aligned Gate-Overlapped LDD Structure", <u>IEDM: Technical Digest of International Electron Devices Meeting</u> , (12/10/2000), pp. 205-208, San Francisco, USA	
MT		MISHIMA, Y. et al., "Improved Lifetime of Poly-Si TFTS with a Self-Aligned Gate-Overlapped LDD Structure", <u>IEEE Transactions on Electron Devices</u> , (06/2002), Vol. 49, No. 6, pp. 981-985	

Examiner Signature	Michael Trinh	Date Considered	3/5/2006
--------------------	---------------	-----------------	----------

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> See Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

<sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> Applicant is to place a check mark here if English language Translation is attached.